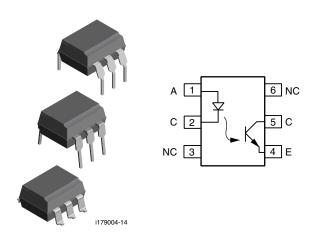


## Vishay Semiconductors

# Optocoupler, Phototransistor Output, no Base Connection



#### **DESCRIPTION**

The CNY17F is an optocoupler consisting of a gallium arsenide infrared emitting diode optically coupled to a silicon planar phototransistor detector in a plastic plug-in DIP-6 package.

The coupling device is suitable for signal transmission between two electrically separated circuits. The potential difference between the circuits to be coupled is not allowed to exceed the maximum permissible reference voltages.

In contrast to the CNY17 series, the base terminal of the F type is not conected, resulting in a substantially improved common-mode interference immunity.

#### **FEATURES**

- Isolation test voltage, 5000 V<sub>RMS</sub>
- No base terminal connection for improved common mode interface immunity
- · Long term stability
- Industry standard dual-in-line package
- Material categorization: For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

# Pb-free



# ROHS

#### **AGENCY APPROVALS**

- UL file no. E52744
- cUL tested to CSA 22.2 bulletin 5A
- DIN EN 60747-5-5 (VDE 0884-5), available with option 1
- BSI: EN 60065, EN 60950-1
- FIMKO
- CQC

ORDERING INFORMATION					
C N Y 1 7 F -	#	X 0 # #	Т	DIP-6	Option 6
PART NUMBER	CTR BIN	PACKAGE OPTION	TAPE AND	₹ 7.62 mm	10.16 mm
	5		REEL	Option 7	Option 9
				> 8 mm	8 mm typ.

AGENCY CERTIFIED/PACKAGE	CTR (%)				
UL, cUL, BSI, FIMKO	40 to 80	63 to 125	100 to 200	160 to 320	
DIP-6	CNY17F-1	CNY17F-2	CNY17F-3	CNY17F-4	
DIP-6, 400 mil, option 6	CNY17F-1X006	CNY17F-2X006	CNY17F-3X006	CNY17F-4X006	
SMD-6, option 7	CNY17F-1X007 (1)	CNY17F-2X007T (1)	CNY17F-3X007T (1)	CNY17F-4X007T (1)	
SMD-6, option 9	CNY17F-1X009T (1)	CNY17F-2X009T (1)	CNY17F-3X009T (1)	CNY17F-4X009T (1)	
VDE, UL, cUL, BSI, FIMKO	40 to 80	63 to 125	100 to 200	160 to 320	
DIP-6	CNY17F-1X001	CNY17F-2X001	CNY17F-3X001	CNY17F-4X001	
DIP-6, 400 mil, option 6	CNY17F-1X016	CNY17F-2X016	CNY17F-3X016	CNY17F-4X016	
SMD-6, option 7	CNY17F-1X017 (1)	CNY17F-2X017 (1)	CNY17F-3X017 (1)	CNY17F-4X017 (1)	
SMD-6, option 9	CNY17F-1X019	CNY17F-2X019 (1)	CNY17F-3X019 (1)	-	

#### Notes

- Additional options may be possible, please contact sales office.
- (1) Also available in tubes; do not put T on end.

4 0 EN 10 V 0 E D E 1 E 1 E D /D 4 0 V 4 0 E



## Vishay Semiconductors

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT							
Reverse voltage		V <sub>R</sub>	6	V			
DC forward current		I <sub>F</sub>	60	mA			
Surge forward current	t ≤ 10 μs	I <sub>FSM</sub>	2.5	А			
Power dissipation		P <sub>diss</sub>	70	mW			
OUTPUT							
Collector emitter breakdown voltage		BV <sub>CEO</sub>	70	V			
Collector current		I <sub>C</sub>	50	mA			
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA			
Output power dissipation		P <sub>diss</sub>	150	mW			
COUPLER							
Isolation test voltage between emitter and detector		V <sub>ISO</sub>	5000	$V_{RMS}$			
Creepage distance			≥ 7	mm			
Clearance distance			≥ 7	mm			
Isolation thickness between emitter and detector			≥ 0.4	mm			
Comparative tracking index per DIN IEC 112/VDE 0303, part 1			≥ 175				
Isolation resistance	V <sub>IO</sub> = 500 V	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω			
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C			
Ambient temperature range		T <sub>amb</sub>	- 55 to + 110	°C			
Junction temperature		Tj	100	°C			
Soldering temperature (1)	2 mm from case, ≤ 10 s	T <sub>sld</sub>	260	°C			
Total power dissipation		P <sub>diss</sub>	220	mW			

#### Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
  implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
  maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to reflow profile for soldering conditions for surface mounted parts (SMD). Refer to wave profile for soldering conditions for through hole parts (DIP).

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	$I_F = 60 \text{ mA}$		$V_{F}$		1.39	1.65	V
Breakdown voltage	I <sub>R</sub> = 10 μA		$V_{BR}$	6			V
Reverse current	V <sub>R</sub> = 6 V		I <sub>R</sub>		0.01	10	μA
Capacitance	$V_R = 0 V$ , $f = 1 MHz$		Co		25		pF
OUTPUT							
Collector emitter capacitance	V <sub>CE</sub> = 5 V, f = 1 MHz		C <sub>CE</sub>		5.2		pF
Base collector capacitance	V <sub>CE</sub> = 5 V, f = 1 MHz		C <sub>BC</sub>		6.5		pF
Emitter base capacitance	V <sub>CE</sub> = 5 V, f = 1 MHz		C <sub>EB</sub>		7.5		pF
COUPLER							
Collector emitter, saturation voltage	$I_F = 10 \text{ mA}, I_C = 2.5 \text{ mA}$		V <sub>CEsat</sub>		0.25	0.4	V
Coupling capacitance			C <sub>C</sub>		0.6		pF
	V 40V	CNY17F-1	I <sub>CEO</sub>		2	50	nA
Oallester will be bed as a second		CNY17F-2	I <sub>CEO</sub>		2	50	nA
Collector emitter, leakage current	V <sub>CE</sub> = 10 V	CNY17F-3	I <sub>CEO</sub>		5	100	nA
		CNY17F-4	I <sub>CEO</sub>		5	100	nA

#### Note

Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering
evaluations. Typical values are for information only and are not part of the testing requirements.



# Vishay Semiconductors

CURRENT TRANSFER RATIO (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION PART SYMBOL MIN. TYP. MAX. U							
		CNY17F-1	CTR	40		80	%	
	I <sub>E</sub> = 10 mA	CNY17F-2		125	%			
l <sub>O</sub> /l <sub>F</sub>	IF = TOTTIA	CNY17F-3 CTR 1		100		200	%	
		CNY17F-4 CTR 160		320	%			
		CNY17F-1	CTR	13	30		%	
	l = 1 mΛ	CNY17F-2	CTR	22	45		%	
	I <sub>F</sub> = 1 mA	CNY17F-3	CTR	34	70		%	
		CNY17F-4	CTR	56	90		%	

#### Note

• Current transfer ratio  $I_C/I_F$  at  $V_{CE}$  = 5 V, 25 °C and collector emitter leakage current by dash number.

<b>SWITCHING CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
LINEAR OPERATION (without	ut saturation)						
Turn-on time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$		t <sub>on</sub>		3		μs
Rise time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$		t <sub>r</sub>		2		μs
Turn-off time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$		t <sub>off</sub>		2.3		μs
Fall time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$		t <sub>f</sub>		2		μs
Cut-off frequency	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$		f <sub>CO</sub>		110		kHz
SWITCHING OPERATION (V	vith saturation)						
	I <sub>F</sub> = 20 mA	CNY17F-1	t <sub>on</sub>		3		μs
Turn-on time	I <sub>E</sub> = 10 mA	CNY17F-2	t <sub>on</sub>		4.2		μs
rum-on time	IF = TO THA	CNY17F-3	t <sub>on</sub>		4.2		μs
	$I_F = 5 \text{ mA}$	CNY17F-4	t <sub>on</sub>		6		μs
	I <sub>F</sub> = 20 mA	CNY17F-1	t <sub>r</sub>		2		μs
Rise time	L = 10 mA	CNY17F-2	t <sub>r</sub>		3		μs
nise time	$I_F = 10 \text{ mA}$	CNY17F-3	t <sub>r</sub>		3		μs
	$I_F = 5 \text{ mA}$	CNY17F-4	t <sub>r</sub>		4.6		μs
	I <sub>F</sub> = 20 mA	CNY17F-1	t <sub>off</sub>		18		μs
Turn-off time	I <sub>F</sub> = 10 mA	CNY17F-2	t <sub>off</sub>		23		μs
Turn-oπ time	IF = TO THA	CNY17F-3	t <sub>off</sub>		23		μs
	I <sub>F</sub> = 5 mA	CNY17F-4	t <sub>off</sub>	_	25		μs
	I <sub>F</sub> = 20 mA	CNY17F-1	t <sub>f</sub>		11		μs
Fall time	10.774	CNY17F-2	t <sub>f</sub>		14		μs
r an unite	I <sub>F</sub> = 10 mA	CNY17F-3	t <sub>f</sub>	_	14		μs
	I <sub>F</sub> = 5 mA	CNY17F-4	t <sub>f</sub>		15		μs



# Vishay Semiconductors

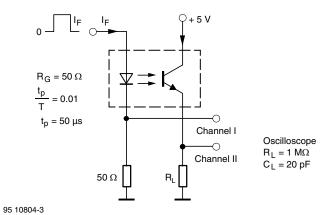


Fig. 1 - Test Circuit, Non-Saturated Operation

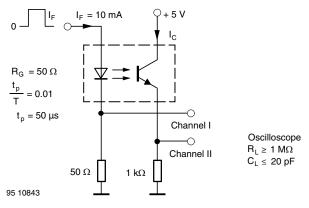


Fig. 2 - Test Circuit, Saturated Operation

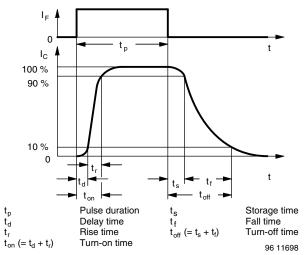


Fig. 3 - Switching Times

### **TYPICAL CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

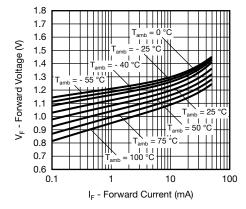


Fig. 4 - Forward Voltage vs. Forward Current

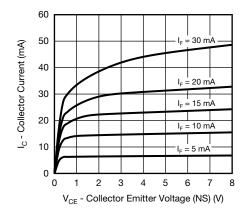


Fig. 5 - Collector Current vs. Collector Emitter Voltage (NS)

Vishay Semiconductors



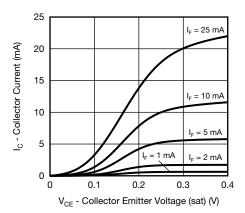


Fig. 6 - Collector Current vs. Collector Emitter Voltage (sat)

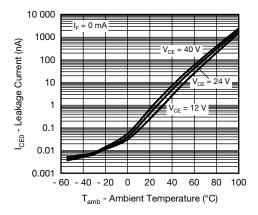


Fig. 7 - Leakage Current vs. Ambient Temperature

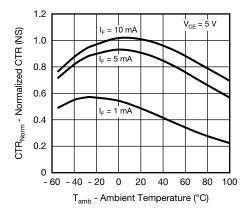


Fig. 8 - Normalized CTR (NS) vs. Ambient Temperature

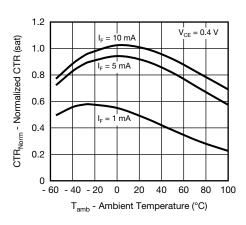


Fig. 9 - Normalized CTR (sat) vs. Ambient Temperature

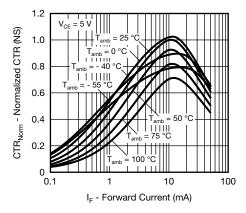


Fig. 10 - Normalized CTR (NS) vs. Forward Current

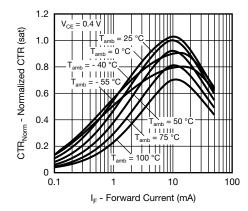


Fig. 11 - Normalized CTR (sat) vs. Forward Current



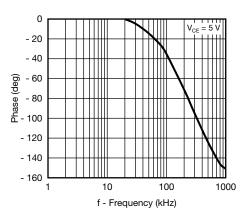


Fig. 12 - CTR Frequency vs. Phase Angle

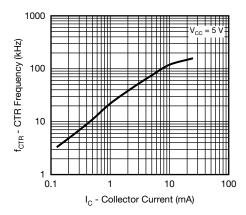


Fig. 13 - CTR Frequency vs. Collector Current

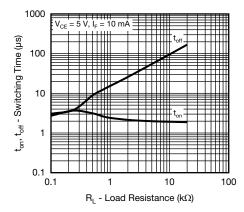
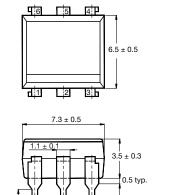


Fig. 14 - Switching Time vs. Load Resistance

# Vishay Semiconductors

## **PACKAGE DIMENSIONS** in millimeters



7.3  $\pm$  0.5

7.62  $\pm$  0.3

1.1  $\pm$  0.1

3.5  $\pm$  0.3

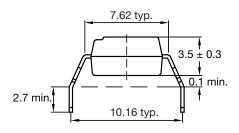
0.5 typ.

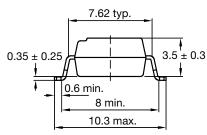
3.3  $\pm$  0.5

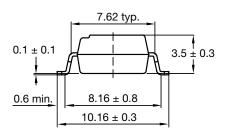
2.54  $\pm$  0.25

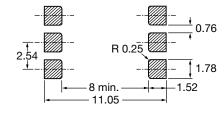
7.62 to 9.98

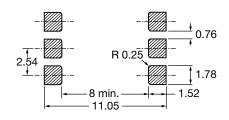
Option 6 Option 7 Option 9





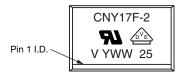






20802-34

#### **PACKAGE MARKING**



#### Notes

- VDE logo is only marked on option 1 parts. Option information is not marked on the part.
- Tape and reel suffix (T) is not part of the package marking.

# Vishay Semiconductors

#### **TUBE AND TAPE INFORMATION**

DEVICES PER TUBE						
TYPE	UNITS/TUBE	TUBES/BOX	UNITS/BOX			
DIP-6	50	40	2000			

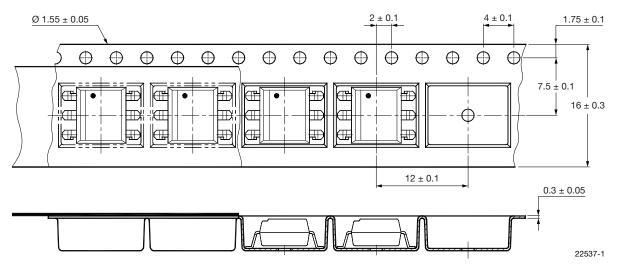


Fig. 15 - Tape and Reel Drawing, 1000 Units per Reel



## **Legal Disclaimer Notice**

Vishay

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000